

### Product Description

The QPF4005 is a dual-channel multi-function Gallium Nitride MMIC front-end module targeted for 39GHz phased array 5G base stations and terminals. For each channel a multi-function MMIC die combines a low noise amplifier, a low insertion-loss high-isolation TR switch, and a high-gain high-efficiency multi-stage PA.

The QPF4005 operates from 37 GHz to 40.5 GHz range. The receive path (LNA + T/R SW) is designed to provide 15dB of gain and a noise figure less than 4.5dB. The transmit path (PA + T/R SW) provides 18 dB of small signal gain and a saturated output power of 2W each channel.

The compact 4.5 mm x 6.0 mm surface mount package configuration is designed to meet the tight lattice spacing requirements and support multi-channel/dual-polarization phased array applications.

The QPF4005 is fabricated on Qorvo's 0.15um GaN on SiC process. It is housed in an air-cavity laminate package with an embedded copper heat slug. The copper slug, coupled with a low thermal resistance die-attach process, allows the QPF4005 to operate at the extreme case temperatures needed in phased array applications.

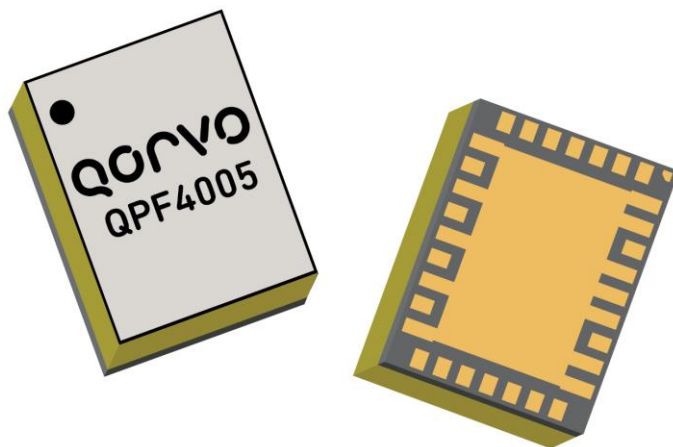
### Product Features

- Frequency Range: 37 – 40.5 GHz <sup>1</sup>
- RX Noise Figure: 4.2 dB
- RX Small Signal Gain: 18 dB
- RX Saturated Power: 17 dBm
- RX TOI : 20 dBm @ - 5 dBm Pin / tone
- TX Small Signal Gain: 23 dB
- TX Saturated Power: 33 dBm
- TX TOI: 42 dBm @ 24 dBm Pout / tone
- TX ACPR: 32dBc @ 24dBm average Pout <sup>2</sup>
- TX Linearity: 4% EVM @ 24 dBm average Pout <sup>2</sup>
- TX PAE: 7% @ 24 dBm average Pout.
- Package Dimensions: 4.5 x 6.0 x 1.8 mm

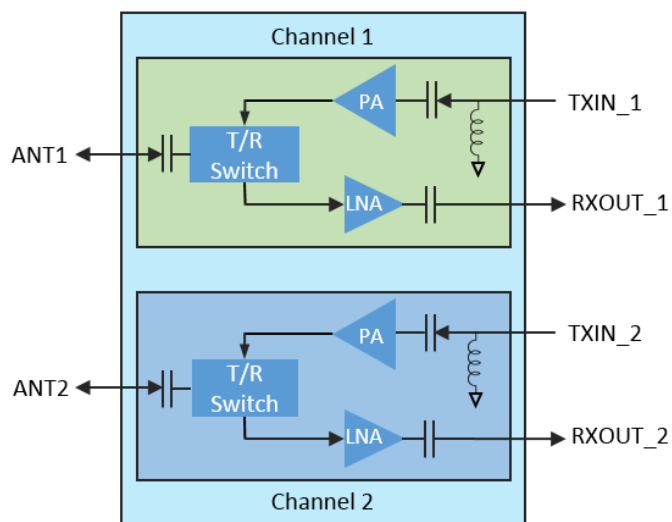
1. Performance is typical at room temperature.
2. OFDM, 400 MHz modulation bandwidth, 64QAM.

### Applications

- 5G Wireless Base stations and terminals
- Point to Point Communications



### Functional Block Diagram



| Part No.     | Description              |
|--------------|--------------------------|
| QPF4005SR    | Tape and Reel, Qty 100   |
| QPF4005EVB03 | QPF4005 Evaluation Board |

### Normal Operating Conditions

| Parameter                                     | Value                                                                            |
|-----------------------------------------------|----------------------------------------------------------------------------------|
| Drain Voltage (TXVD, RXVD) <sup>1, 2, 5</sup> | 20 V                                                                             |
| Drain Current (TXIDQ12 / TXIDQ3)              | 135 mA / 24 mA <sup>4</sup>                                                      |
| Drain Current (RXIDQ)                         | 15 mA                                                                            |
| Gate Voltage (TXVG12 / TXVG3) <sup>3</sup>    | -2 V / -2.4 V                                                                    |
| Gate Voltage (RXVG) <sup>3</sup>              | -2 V                                                                             |
| Control Voltage (TXSW, RXSW)                  | TXSW = 0 V, RXSW = 20V (RX on, TX off)<br>TXSW = 20 V, RXSW = 0V (RX off, TX on) |
| Operating Temperature Range                   | -40 to 95 °C                                                                     |

- 1 Electrical specifications are measured at specified test conditions, no guarantee over all recommended operating conditions
- 2 Suffixes for channel ID removed from pin labels, both channels use the same settings
- 3 Gate voltages shown are typical, can be adjusted to set required drain current
- 4 Other current settings: 45 / 60 mA = 105 mA; 90 / 120 mA = 210 mA; 135 / 180 mA = 315 mA (gate controls combined together)
- 5 When in TX mode, the drain of receive channel is turned off by an internal switch.

### Electrical Specifications RX

Test conditions, unless otherwise noted: VD = 20 V, IDQ = 15 mA. Data de-embedded to device reference planes, 25 °C

| Parameter                                            | Min | Typical | Max  | Units |
|------------------------------------------------------|-----|---------|------|-------|
| Frequency                                            | 37  |         | 40.5 | GHz   |
| Small Signal Gain                                    |     | 18      |      | dB    |
| Noise Figure                                         |     | 4.2     |      | dB    |
| Saturated Output Power                               |     | 17      |      | dBm   |
| Input Return Loss                                    |     | 12      |      | dB    |
| Output Return Loss                                   |     | 15      |      | dB    |
| Output TOI, @ -5 dBm Pin / tone, 10 MHz tone spacing |     | 20      |      | dBm   |
| Gain Temperature Coefficient                         |     | -0.056  |      | dB/°C |

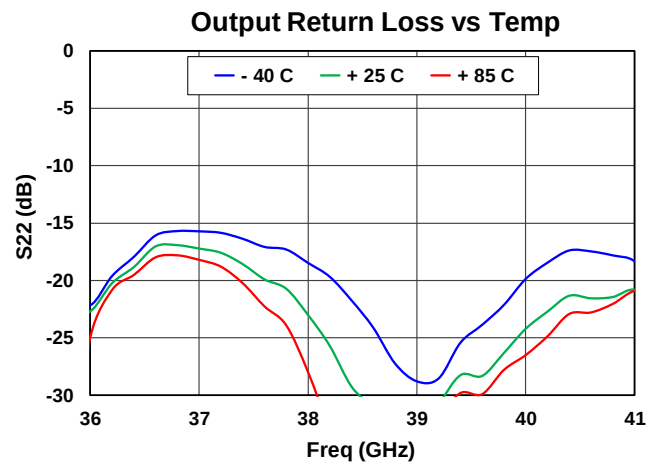
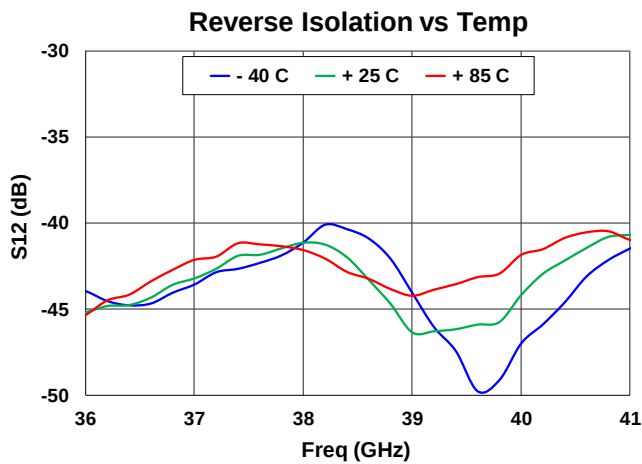
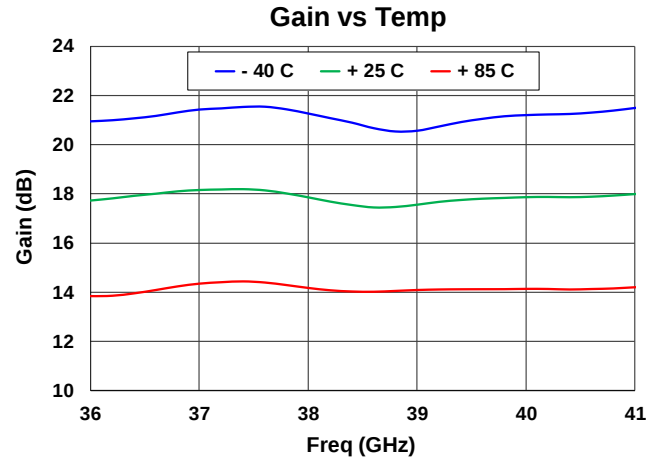
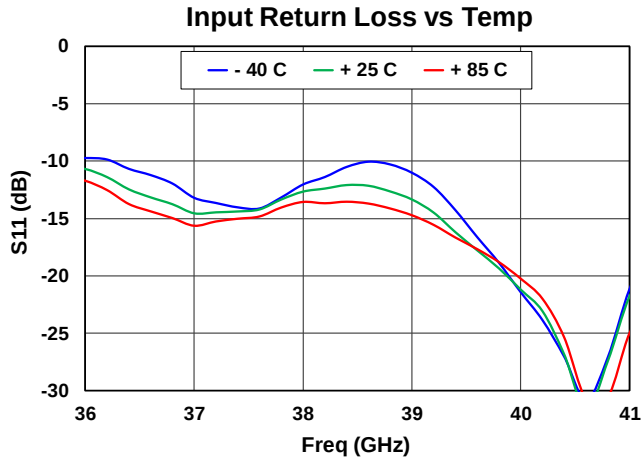
### Electrical Specifications TX

Test conditions unless otherwise noted: VD = 20 V, TXIDQ12 / TXIDQ3 = 135mA / 24 mA  
Data de-embedded to device reference planes, 25 °C

| Parameter                                            | Min | Typical | Max  | Units |
|------------------------------------------------------|-----|---------|------|-------|
| Frequency                                            | 37  |         | 40.5 | GHz   |
| Small Signal Gain                                    |     | 23      |      | dB    |
| Saturated Output Power                               |     | 33      |      | dBm   |
| Input Return Loss                                    |     | 12      |      | dB    |
| Output Return Loss                                   |     | 13      |      | dB    |
| Output TOI, @ 24dBm Pout / tone, 10 MHz tone spacing |     | 42      |      | dBm   |
| ACPR (24 dBm average power, OFDM, 400MHz, 64QAM)     |     | -32     |      | dBc   |
| EVM (24 dBm average power, OFDM, 400MHz, 64QAM)      |     | 4       |      | %     |
| PAE at average output power (24dBm)                  |     | 7       |      | %     |
| Gain Temperature Coefficient                         |     | -0.112  |      | dB/°C |

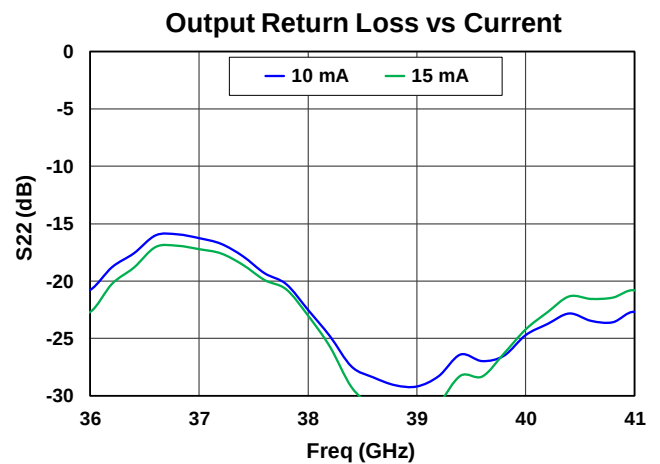
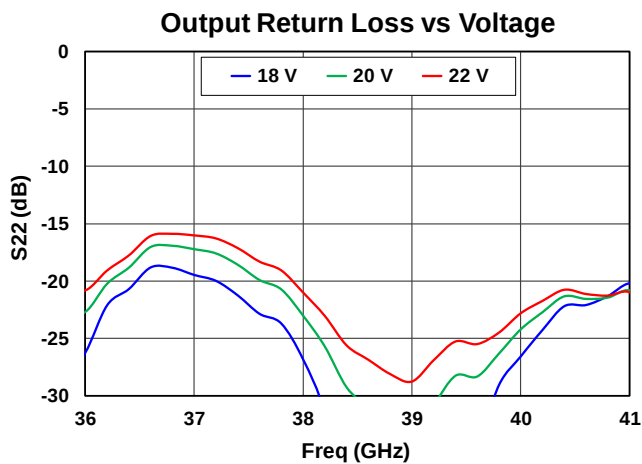
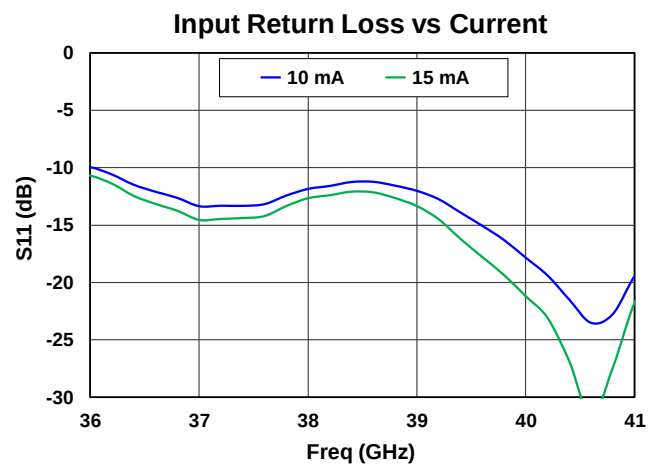
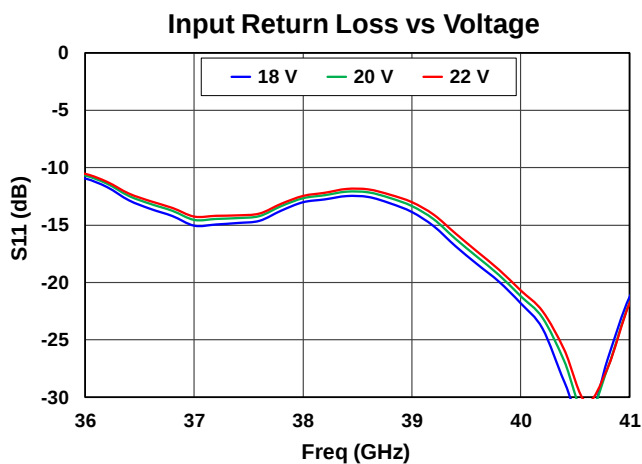
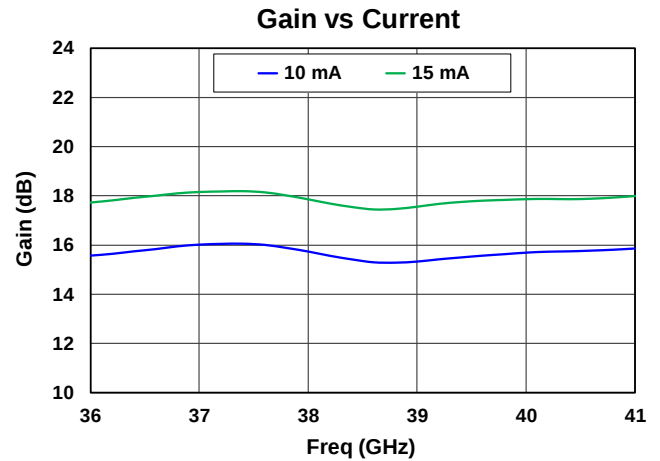
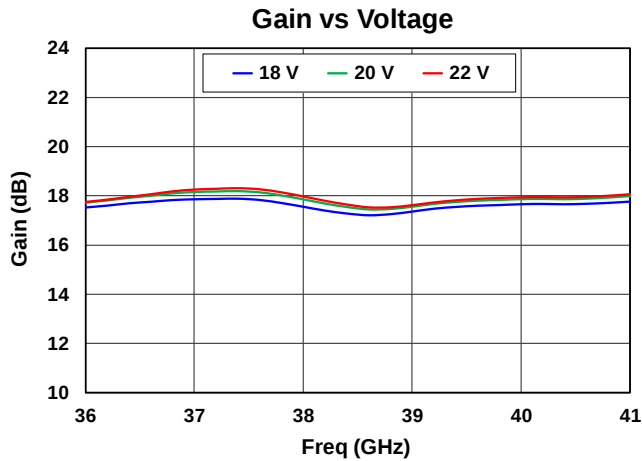
### Performance Plots, Small Signal, Receive Path

Test Conditions unless otherwise stated: RXVD = 20 V, RXIDQ = 15 mA, 25C



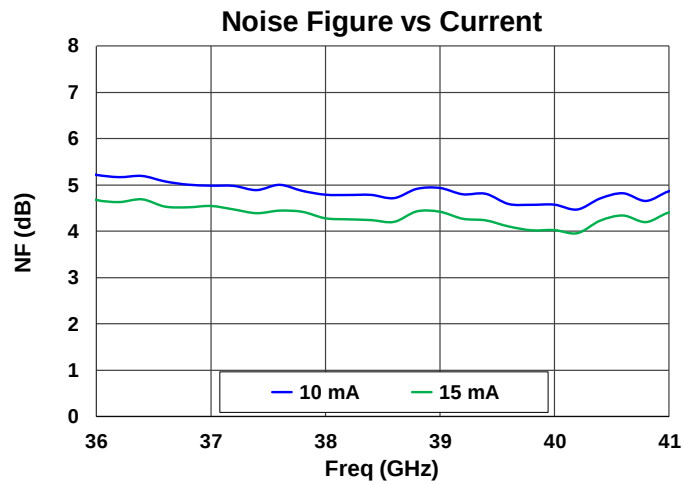
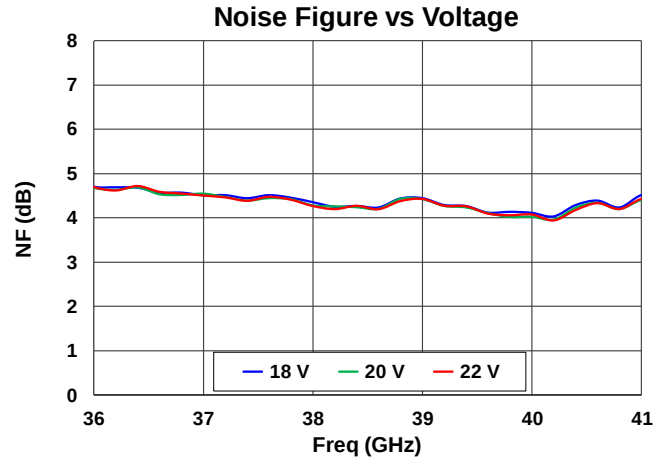
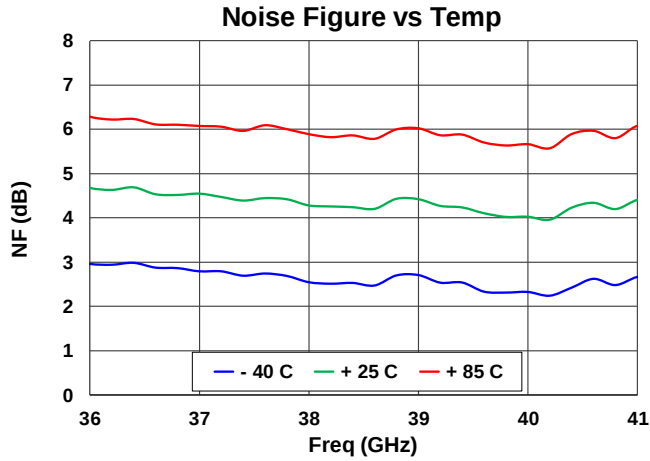
### Performance Plots, Small Signal, Receive Path

Test Conditions unless otherwise stated: RXVD = 20 V, RXIDQ = 15 mA, 25 C



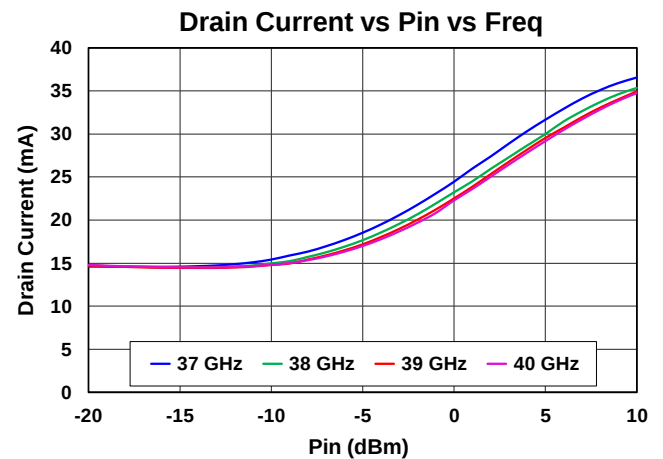
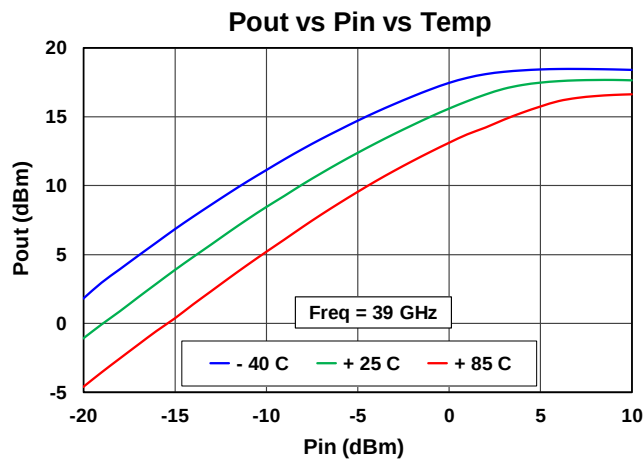
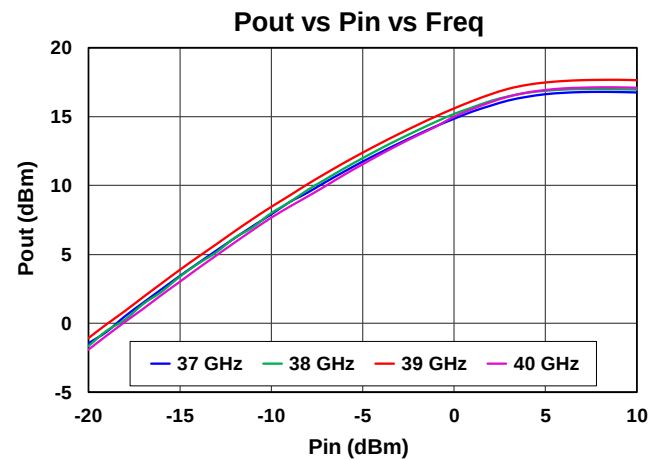
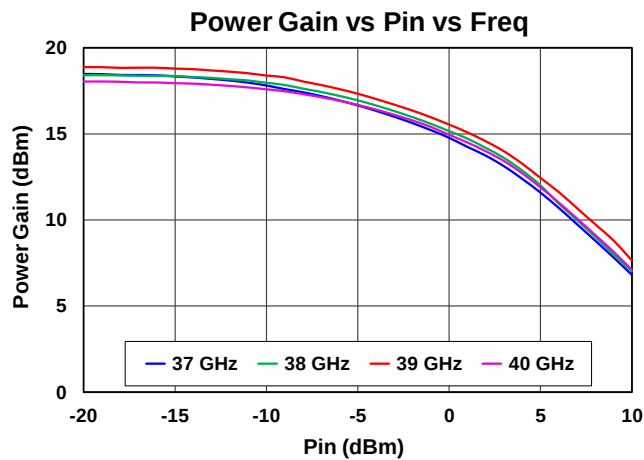
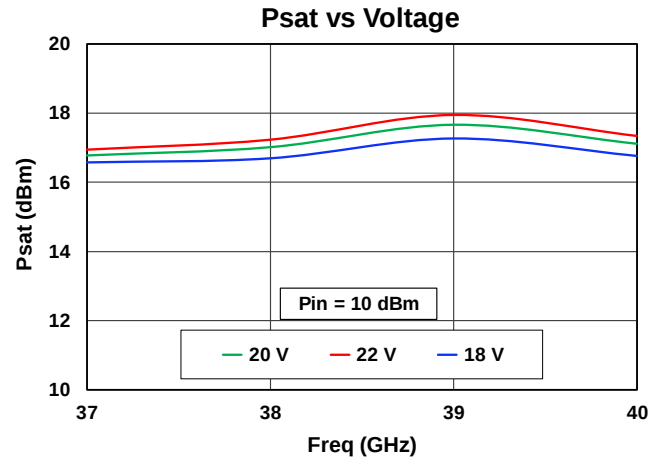
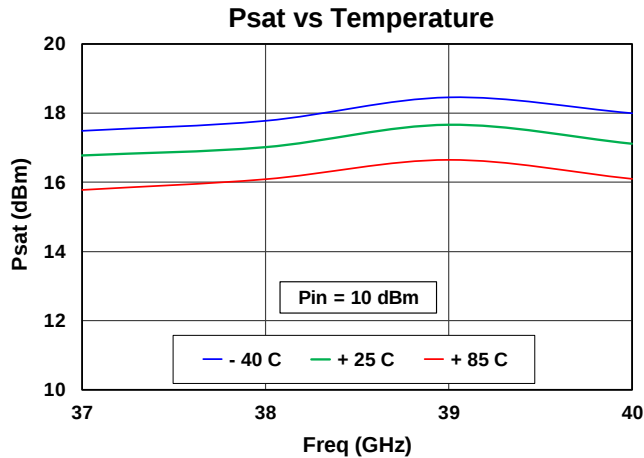
### Performance Plots, Noise Figure, Receive Path

Test Conditions unless otherwise stated: RXVD = 20 V, RXIDQ = 15 mA, 25 C



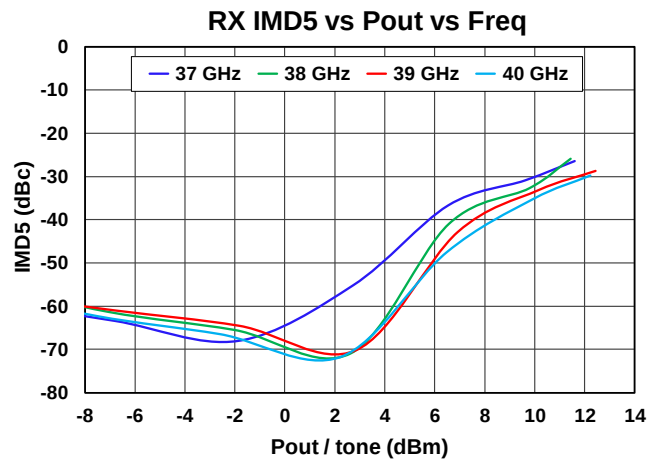
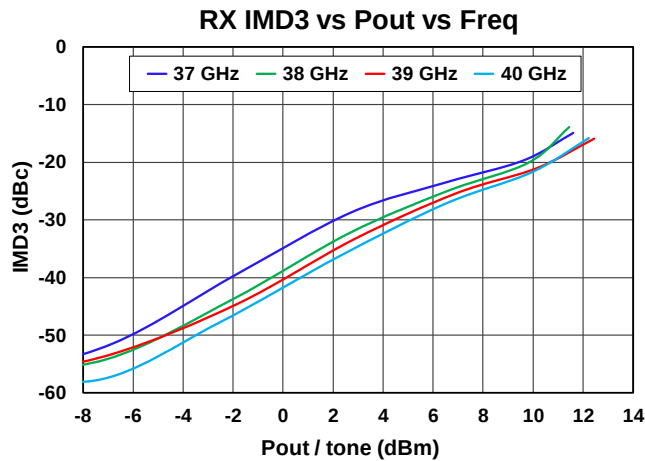
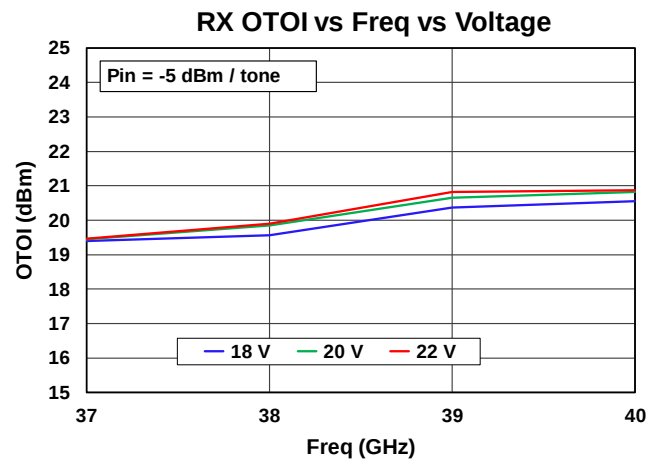
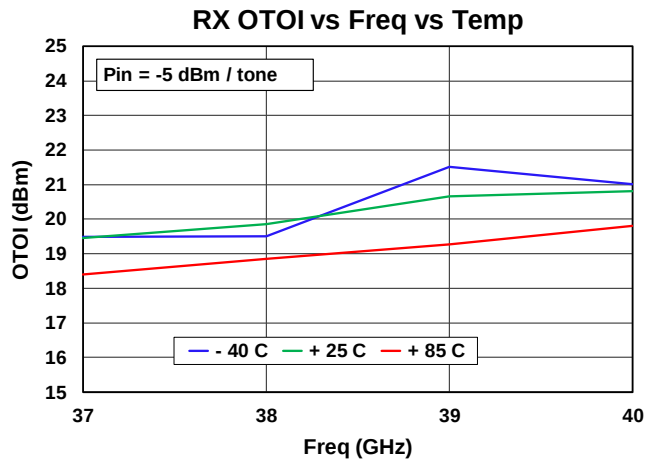
### Performance Plots, Large Signal, Receive Path

Test Conditions unless otherwise stated: RXVD = 20 V, RXIDQ = 15 mA, CW, 25 C



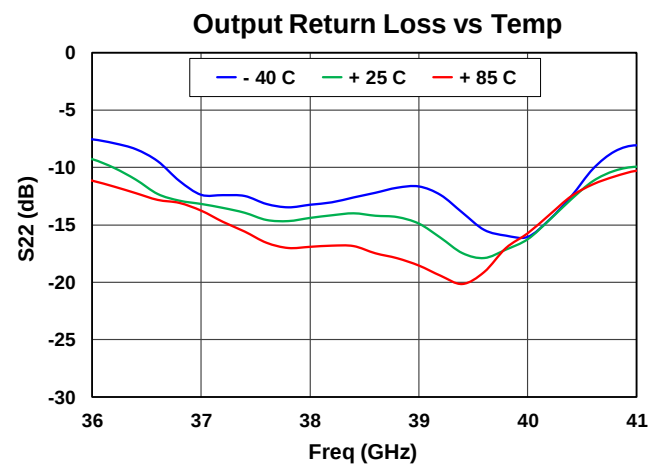
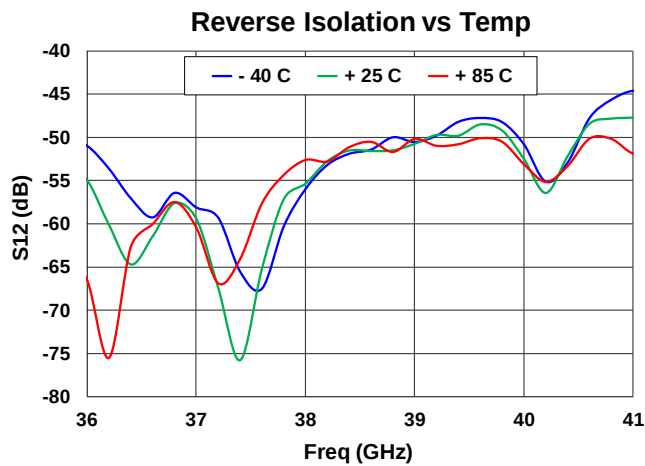
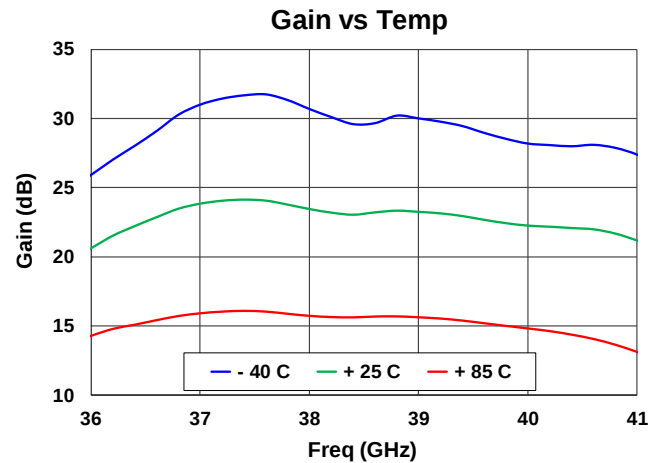
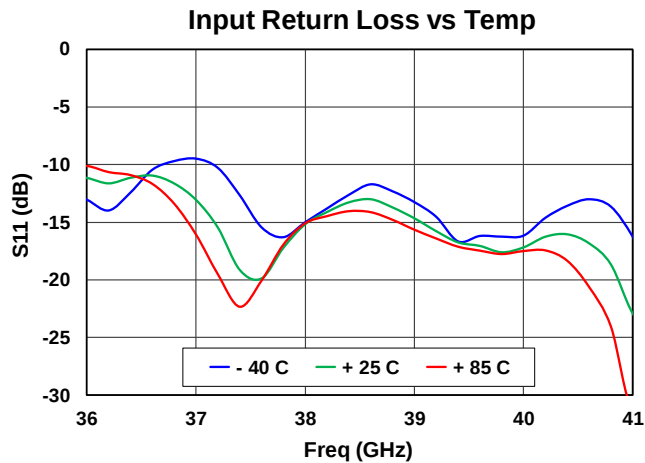
### Performance Plots, Linearity, Receive Path

Test Conditions unless otherwise stated: RXVD = 20 V, RXIDQ = 15 mA, Tone spacing: 10 MHz, 25 C



### Performance Plots, Small Signal, Transmit Path

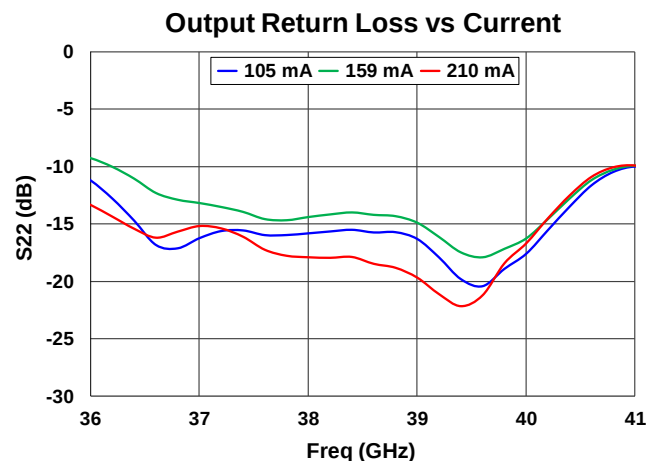
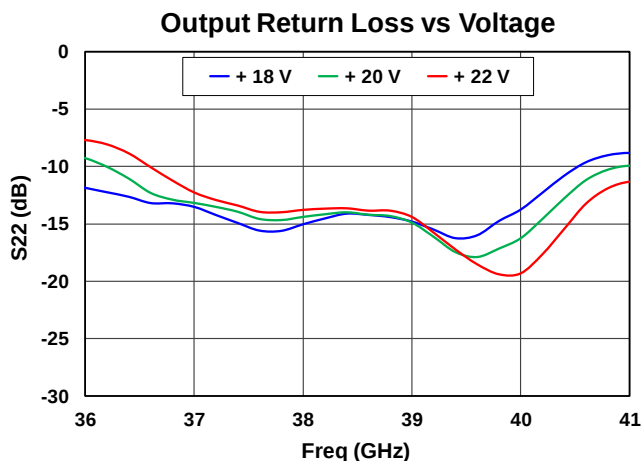
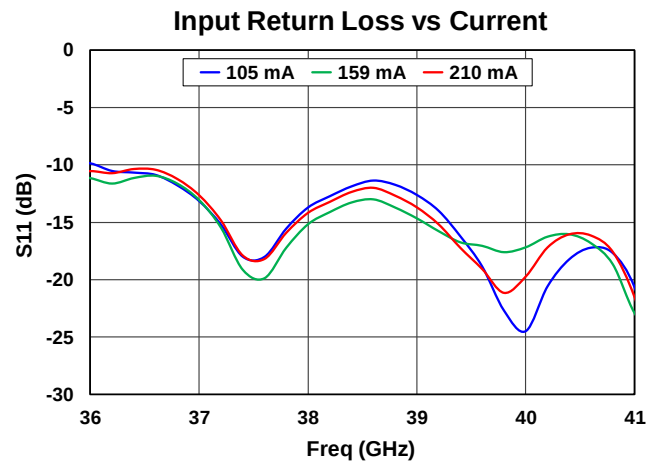
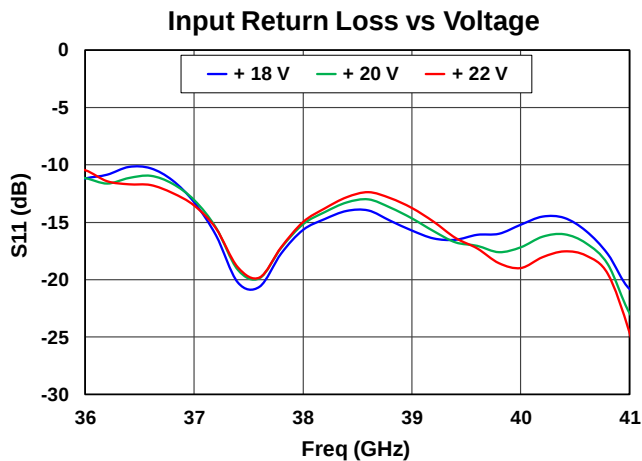
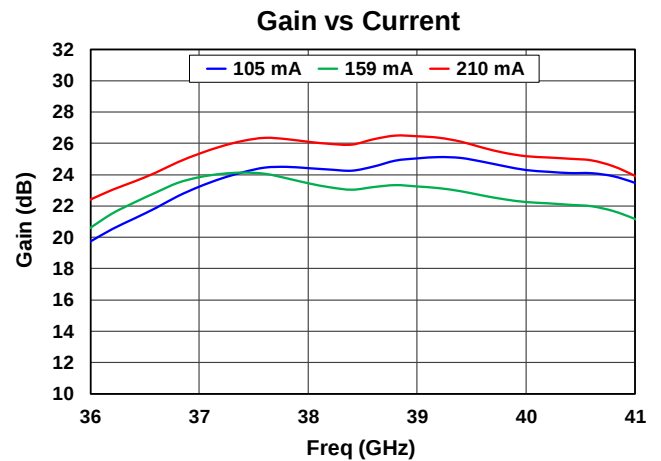
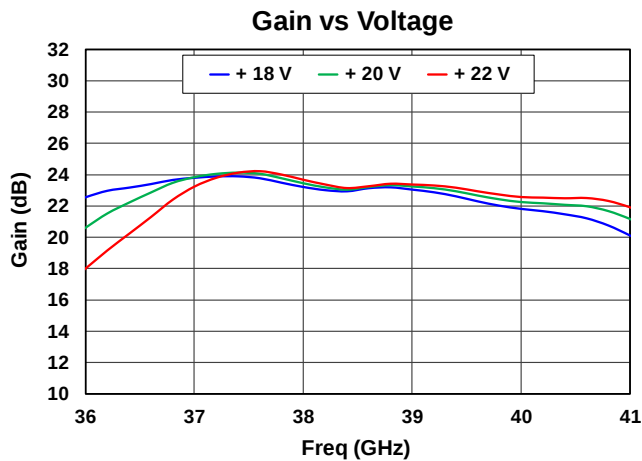
Test Conditions unless otherwise stated: TXVD = 20 V, TXIDQ12 = 135 mA, TXIDQ3 = 24 mA



### Performance Plots, Small Signal, Transmit Path

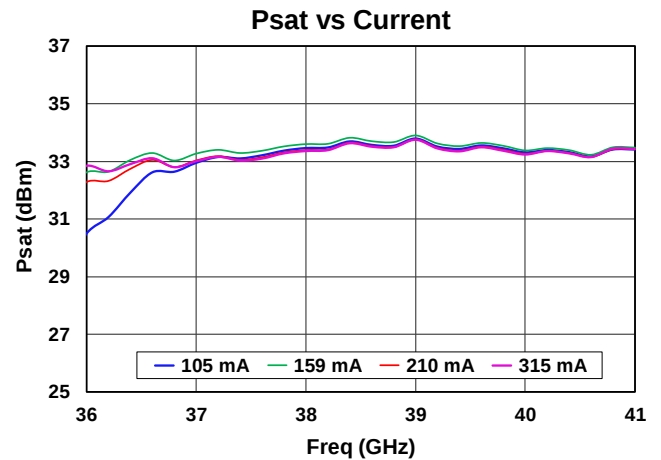
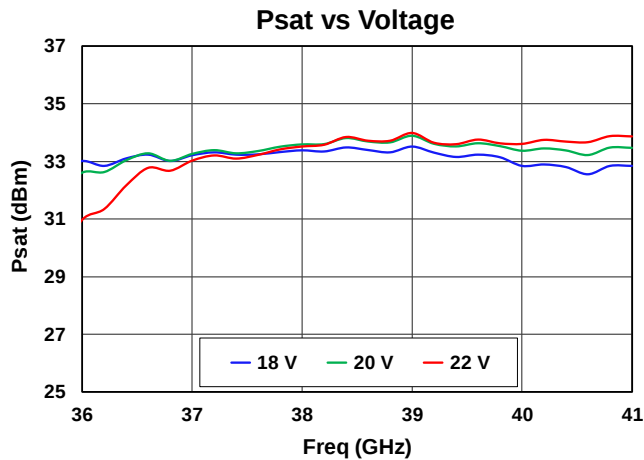
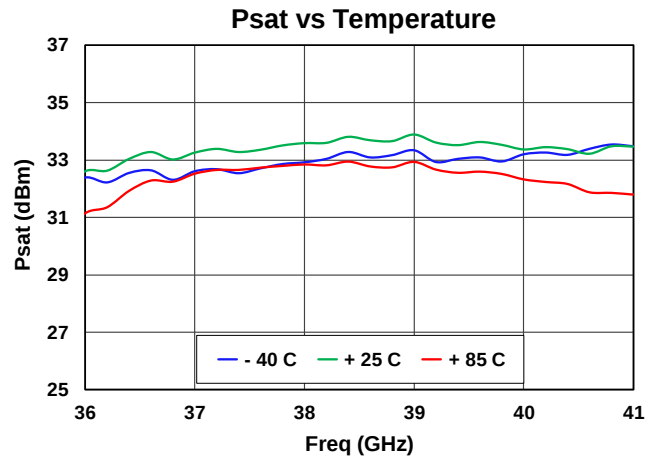
Test Conditions unless otherwise stated: TXVD = 20 V, 25 C

TXIDQ12 = 135 mA, TXIDQ3 = 24 mA (159mA), for other bias conditions refer to Nominal Operating Condition table in page 2



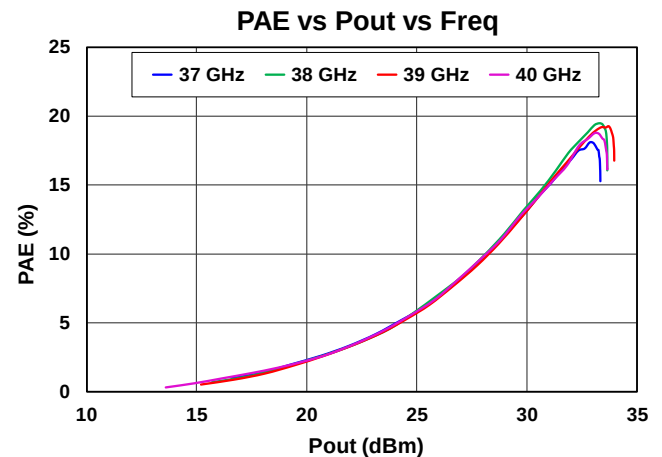
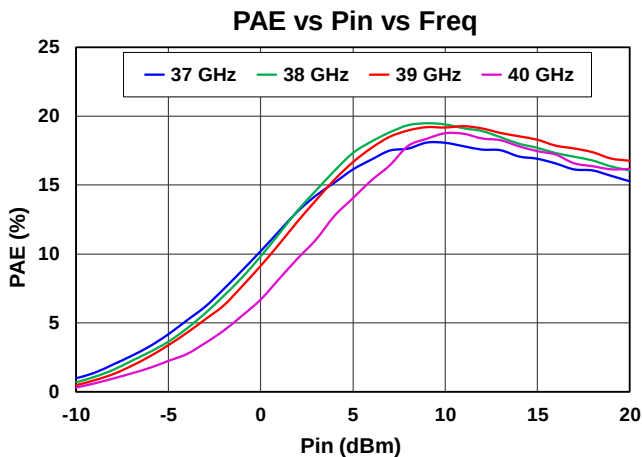
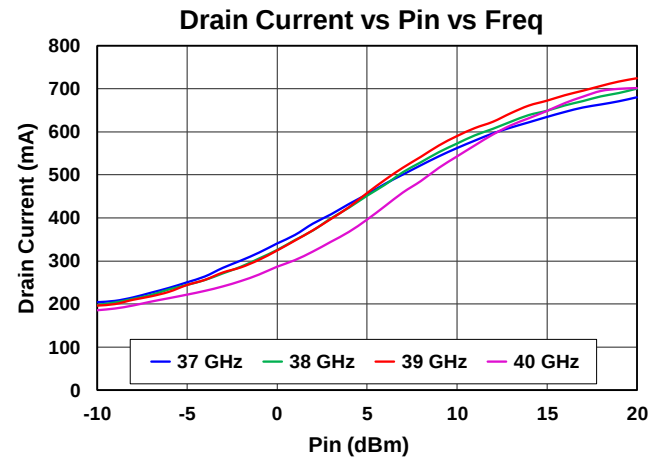
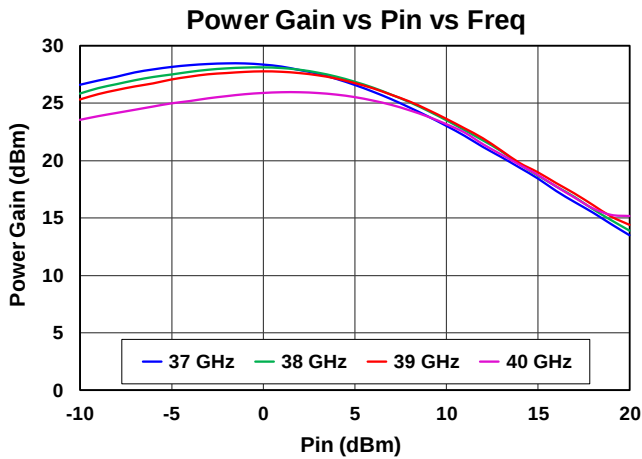
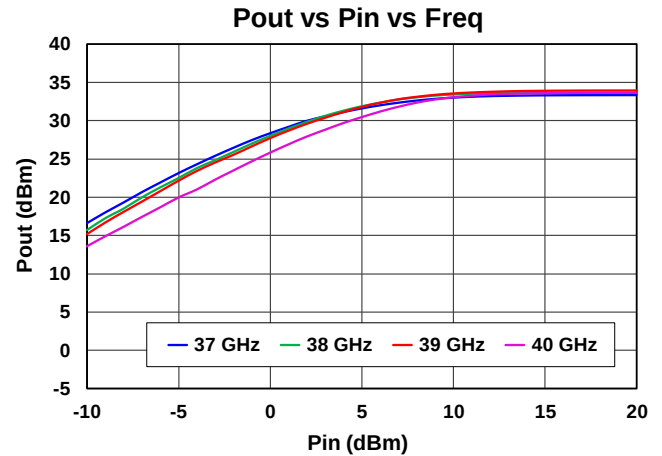
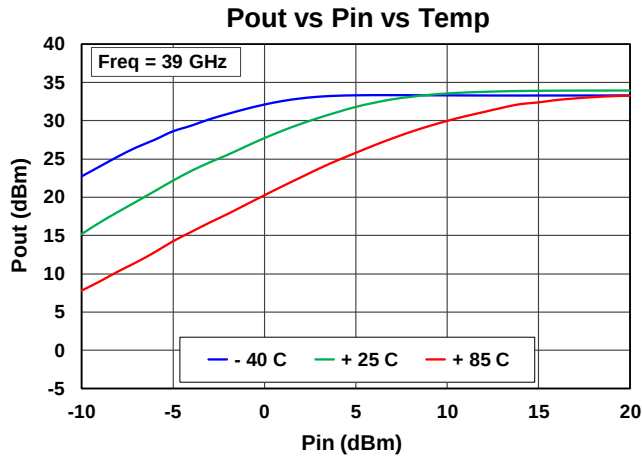
### Performance Plots, Large Signal, Transmit Path

Test Conditions unless otherwise stated: TXVD = 20 V, 25 C, Pin = 20 dBm  
TXIDQ12 = 135 mA, TXIDQ3 = 24 mA (159mA), for other bias conditions refer to Nominal Operating Condition table in page 2



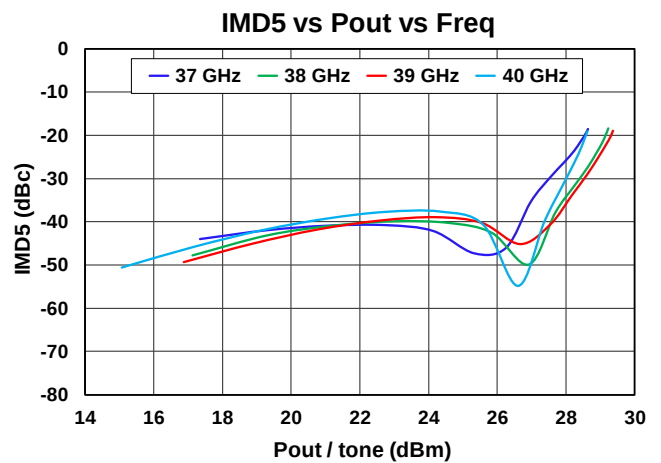
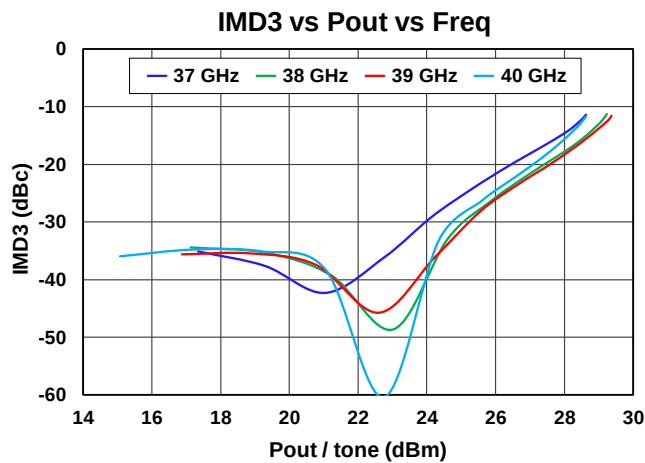
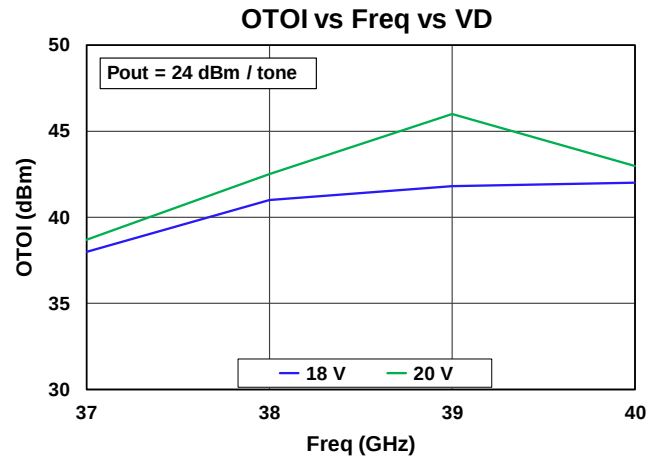
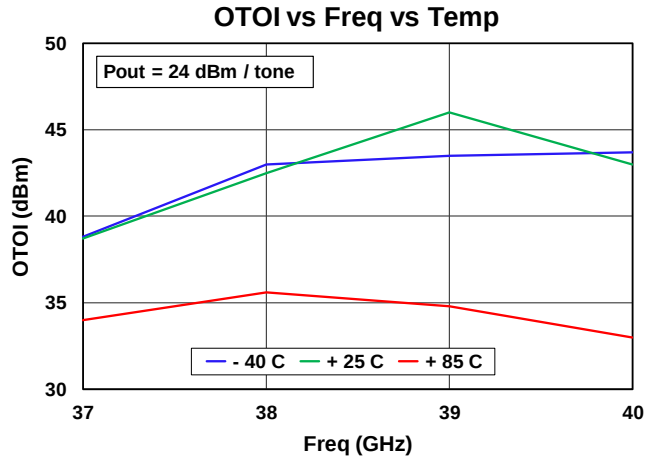
### Performance Plots, Large Signal, Transmit Path

Test Conditions unless otherwise stated: TXVD = 20 V, TXIDQ12 = 135 mA, TXIDQ3 = 24 mA,  
Pulse Mode: PW = 100  $\mu$ s, DC = 10%, 25C



### Performance Plots, Linearity, Transmit Path

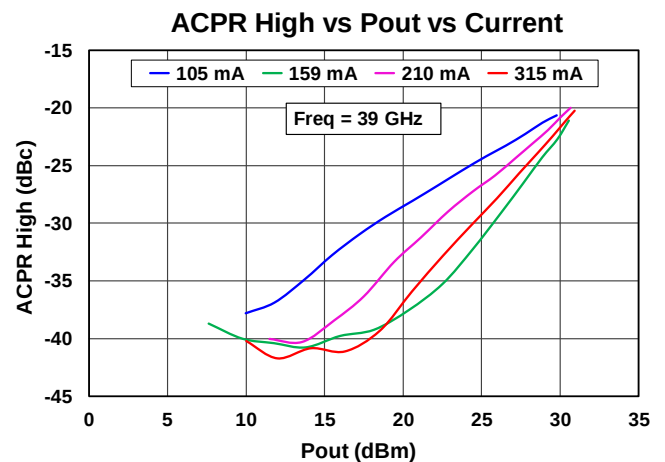
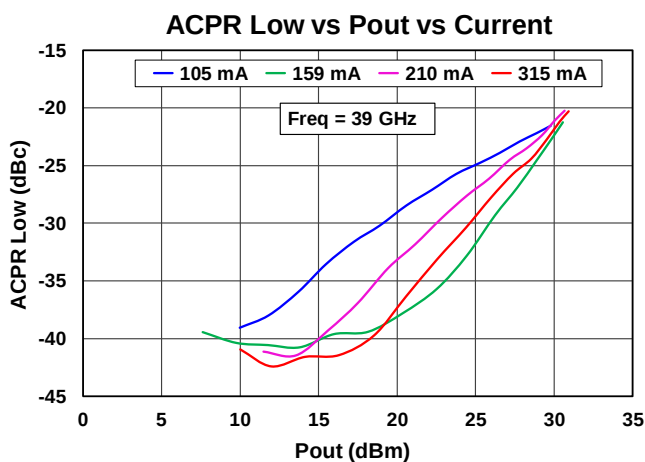
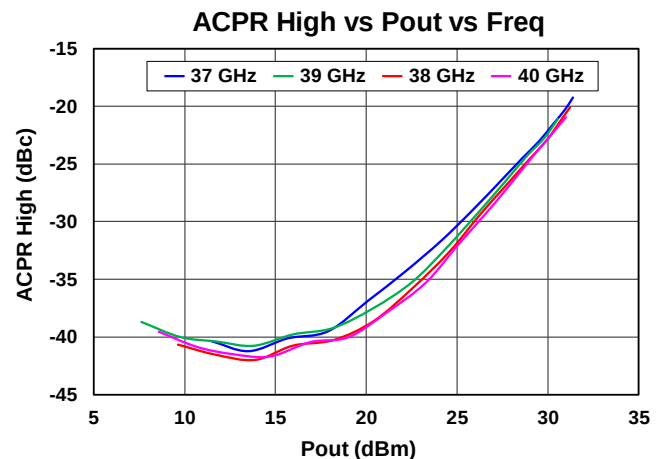
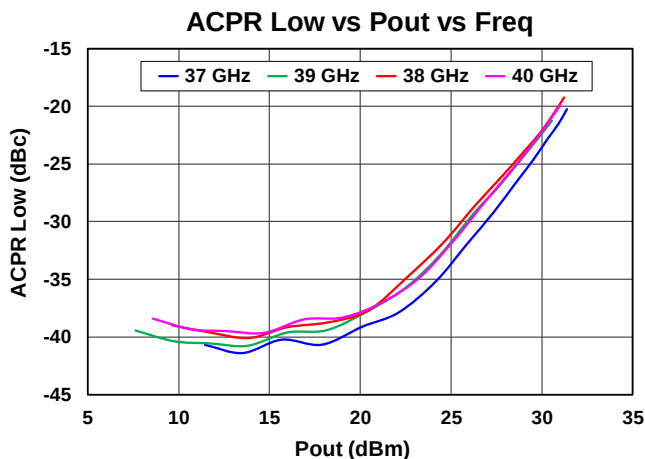
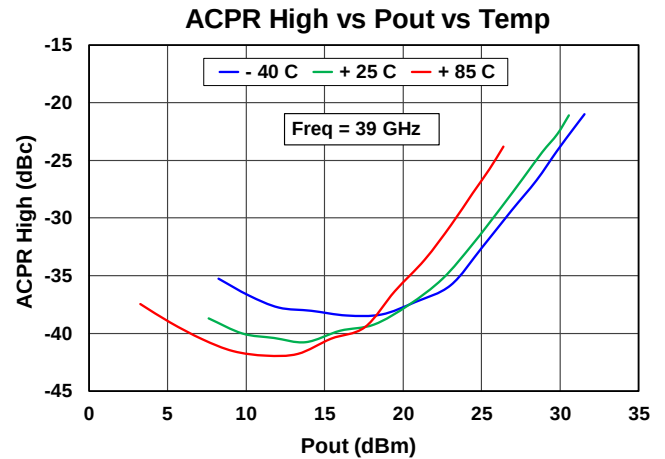
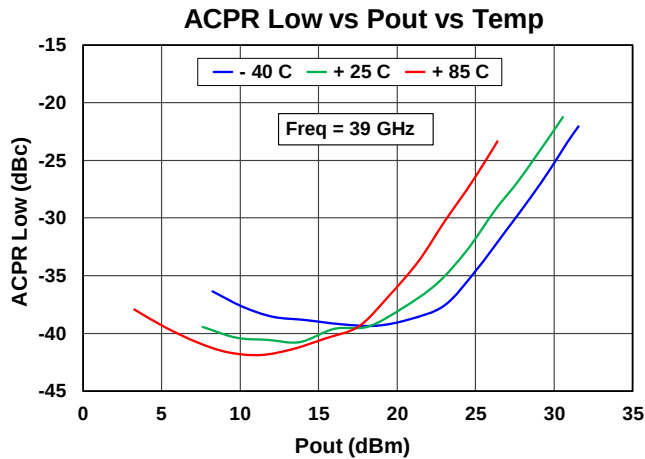
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### Performance Plots, Modulated Signal, Transmit Path

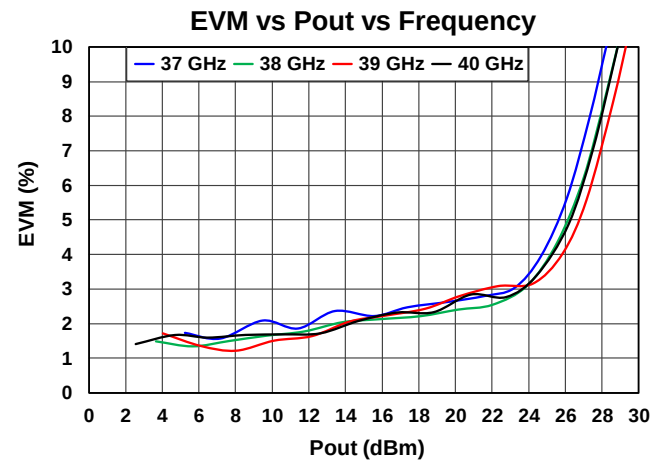
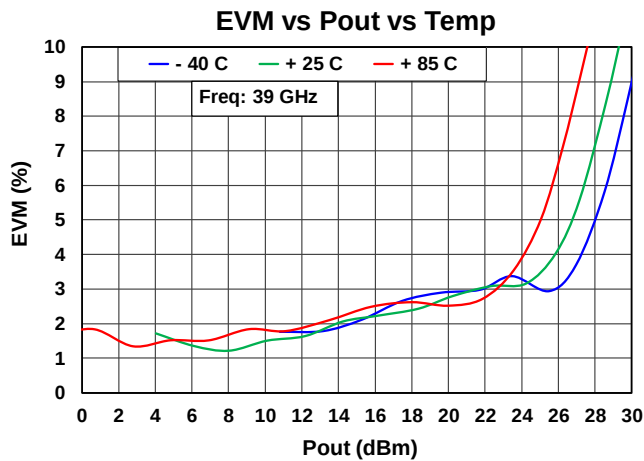
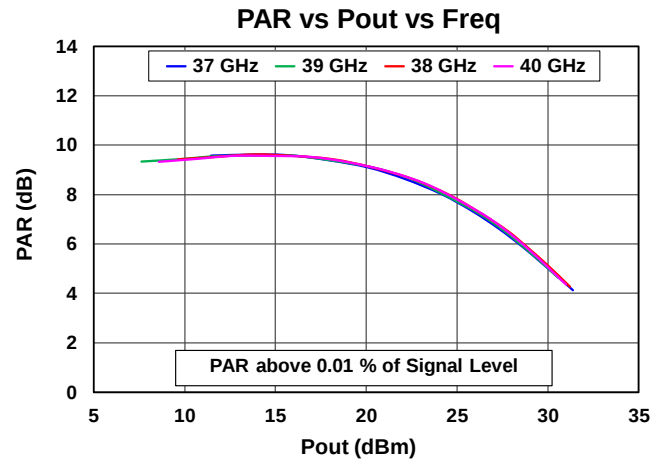
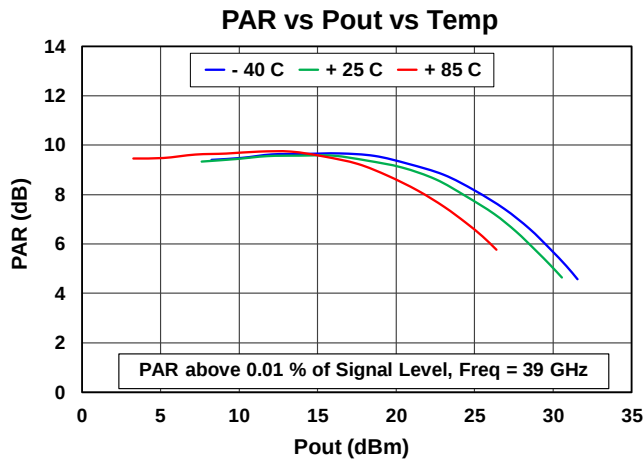
Test Conditions unless otherwise stated: TXVD = 20 V, 25 C

TXIDQ12 = 135 mA, TXIDQ3 = 24 mA (159mA), for other bias conditions refer to Nominal Operating Condition table in page 2



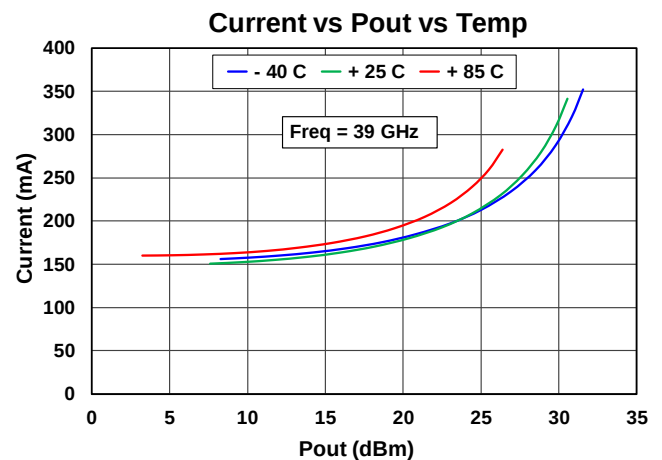
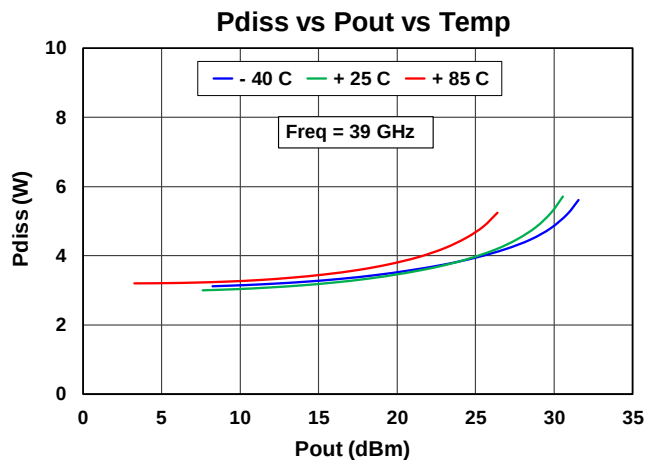
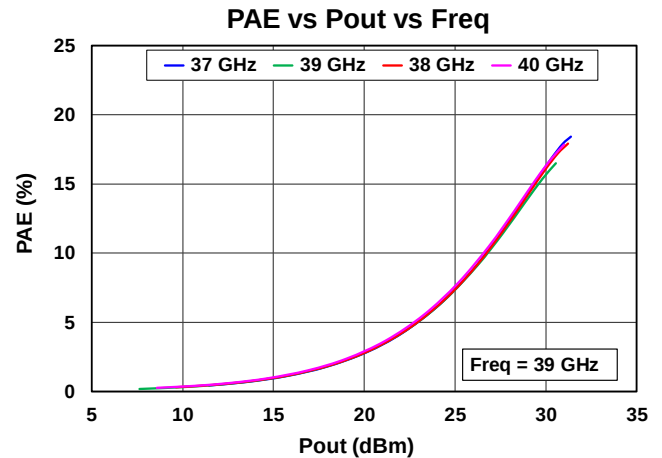
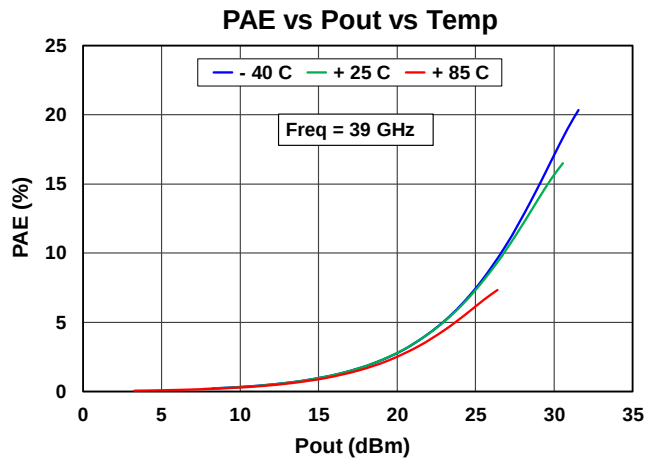
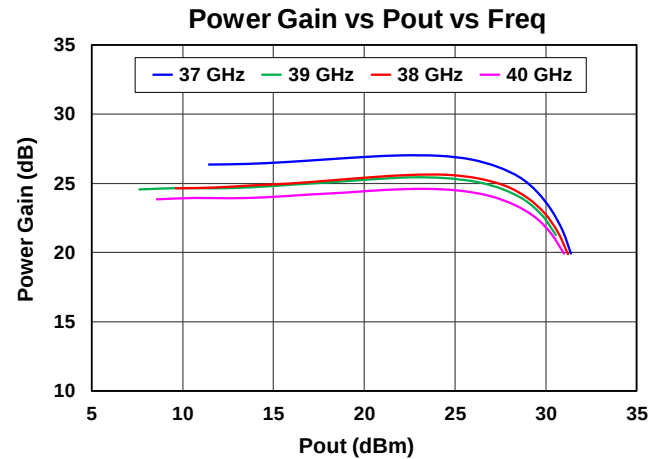
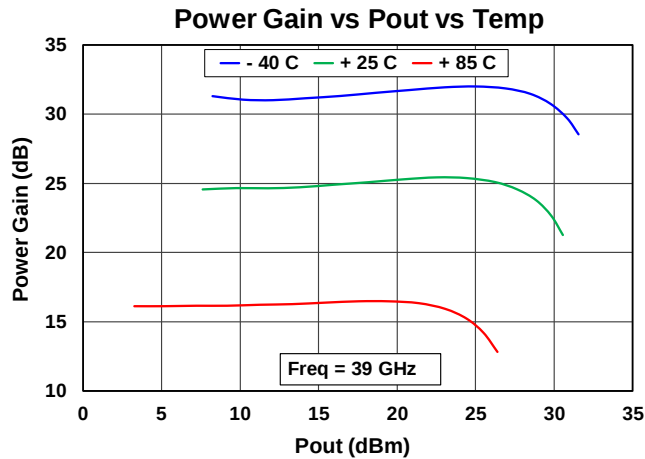
### Performance Plots, Modulated Signal, Transmit Path

Test Conditions unless otherwise stated: TXVD = 20 V, TXIDQ12 = 135 mA, TXIDQ3 = 24 mA  
Source: 400 MHz OFDM, 64 QAM, 25 C



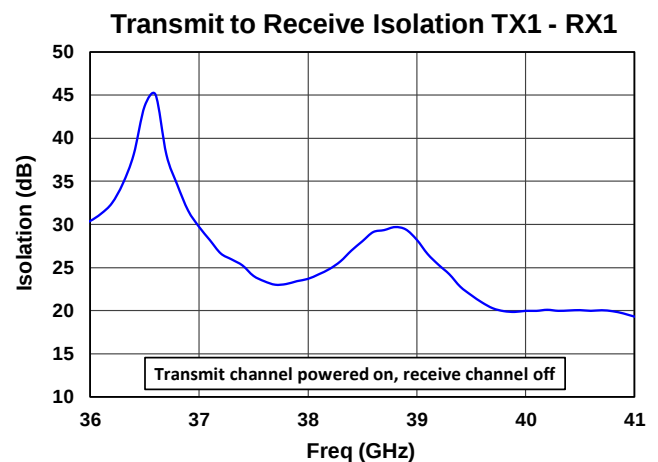
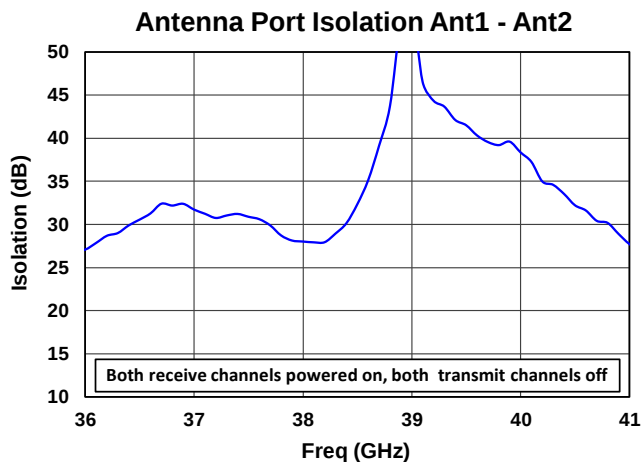
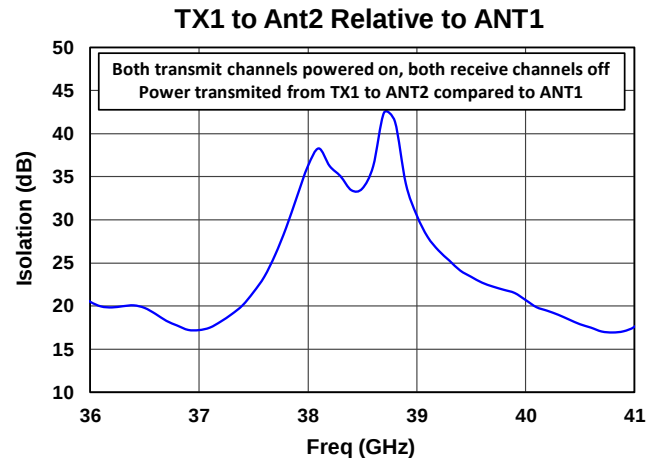
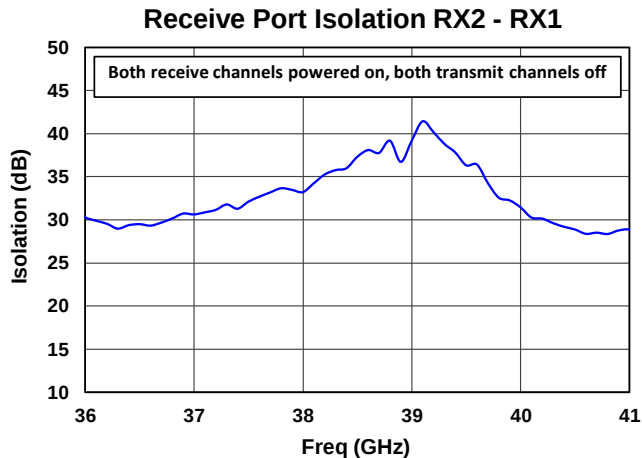
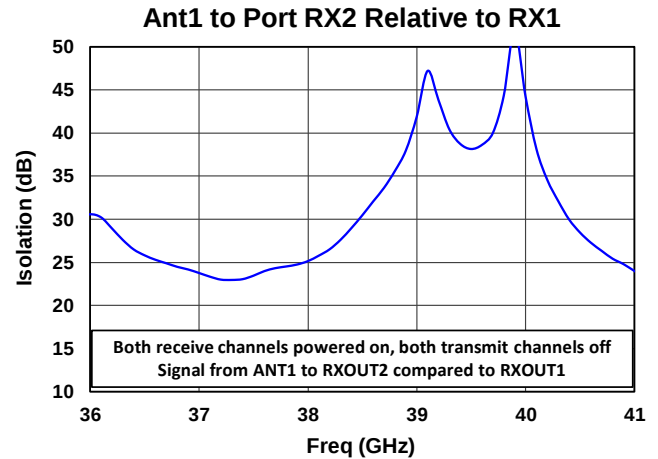
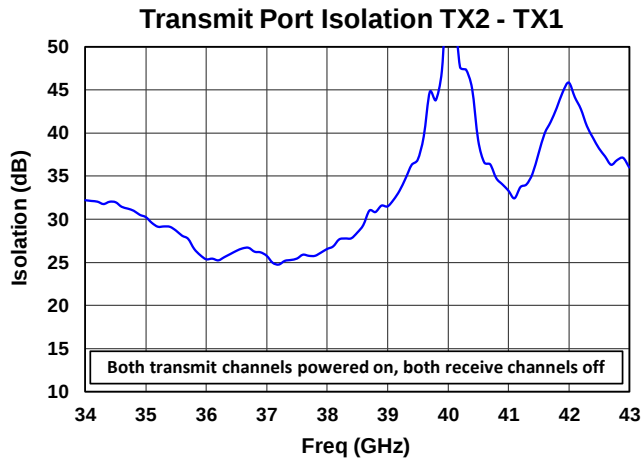
### Performance Plots, Modulated Signal, Transmit Path

Test Conditions unless otherwise stated: TXVD = 20 V, TXIDQ12 = 135 mA, TXIDQ3 = 24 mA  
Source: 400 MHz OFDM, 64 QAM, 25 C

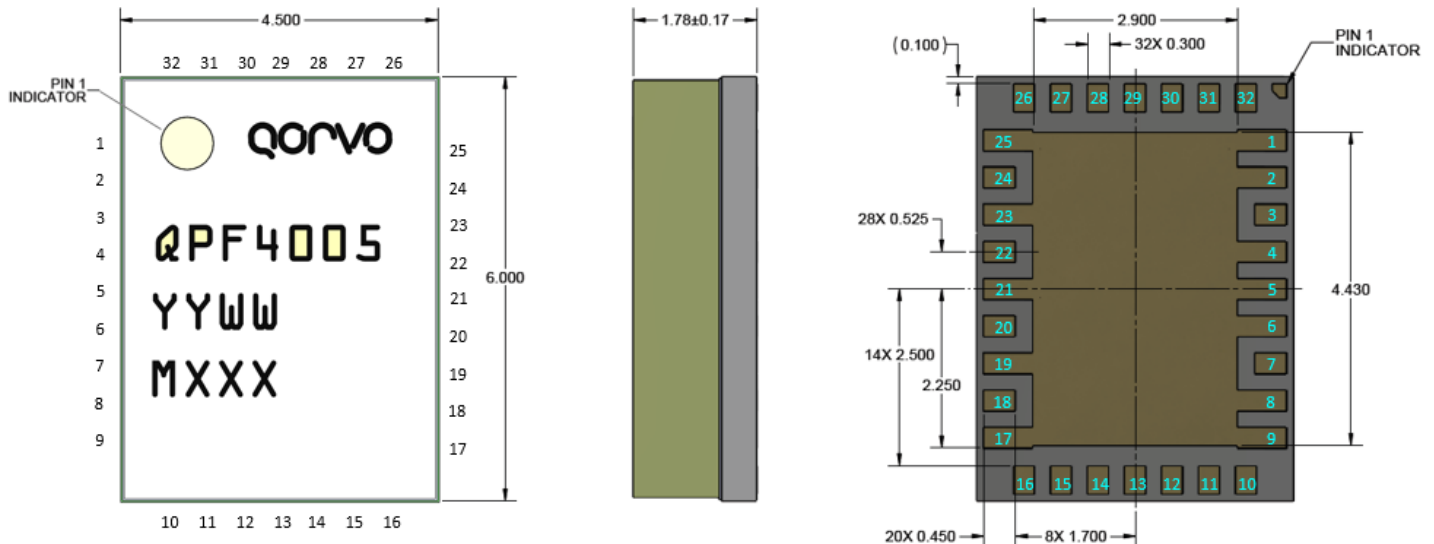


### Performance Plots, Channel Isolations

Test Conditions unless otherwise stated: TXVD = 20 V, TXIDQ12 = 135 mA, TXIDQ3 = 24 mA, RXVD = 20 V, RXID = 15 mA  
Cable calibration, data not de-embedded, 25 C



### Mechanical Drawings & Pad Descriptions

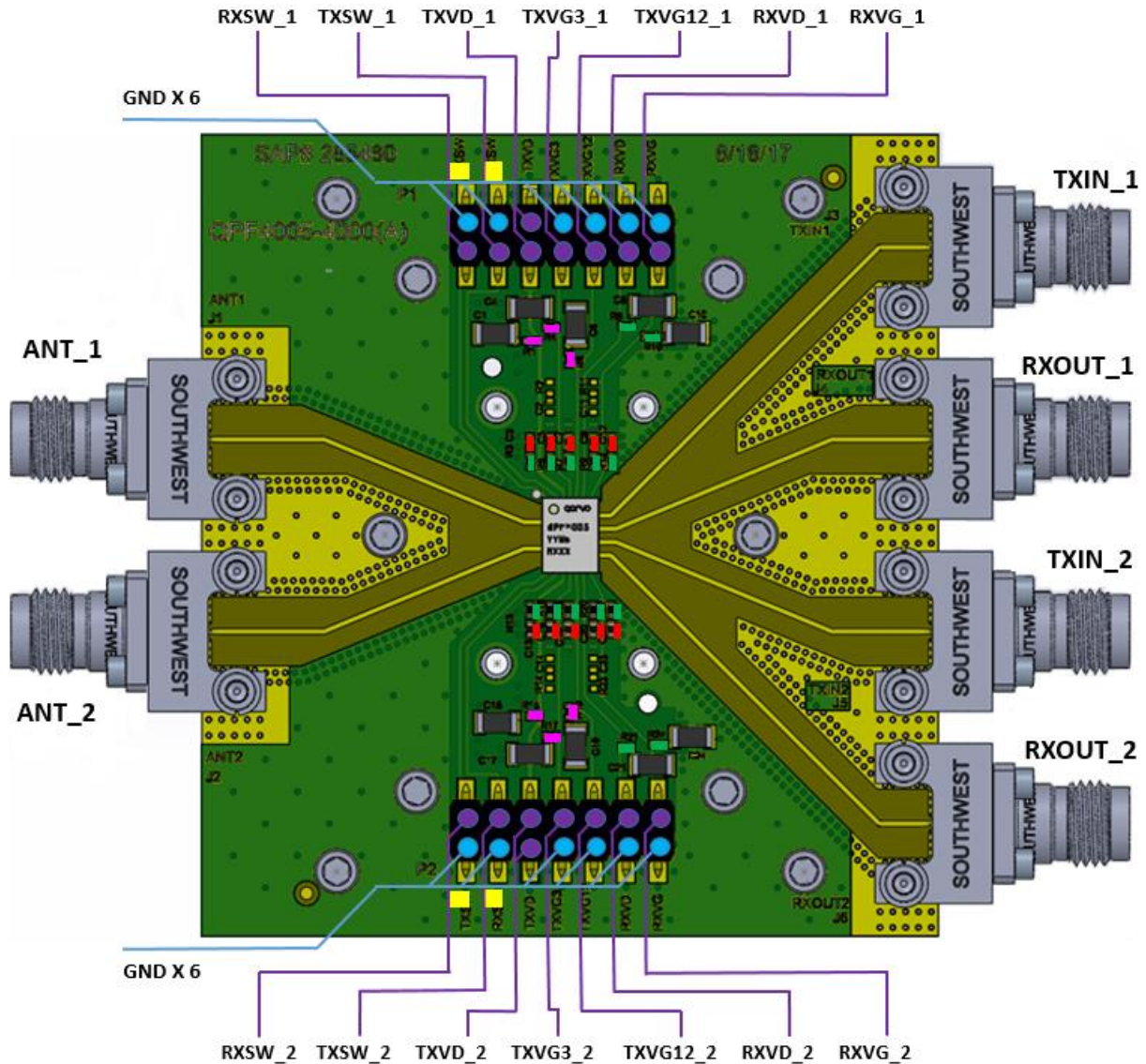


Dimensions in mm, Part Marking:

QPF4005: Part Number, YY = Part Assembly Year, WW = Part Assembly Week, MXXX = Batch ID

| Pin Number               | Label    | Description               |
|--------------------------|----------|---------------------------|
| 1, 2, 4, 5, 6, 8, 9      | GND      | GROUND                    |
| 3                        | ANT_1    | Channel 1 Antenna         |
| 22                       | RXOUT_1  | Channel 1 Receive Output  |
| 24                       | TXIN_1   | Channel 1 Transmit Input  |
| 26                       | RXVG_1   | Channel 1 Receive VG      |
| 27                       | RXVD_1   | Channel 1 Receive VD      |
| 28                       | TXVG12_1 | Channel 1 Transmit VG12   |
| 29                       | TXVG3_1  | Channel 1 Transmit VG3    |
| 30                       | TXVD_1   | Channel 1 Transmit VD     |
| 31                       | TXSW_1   | Channel 1 Transmit Switch |
| 32                       | RXSW_1   | Channel 1 Receive Switch  |
| 7                        | ANT_2    | Channel 2 Antenna         |
| 10                       | RXSW_2   | Channel 2 Receive Switch  |
| 11                       | TXSW_2   | Channel 2 Transmit Switch |
| 12                       | TXVD_2   | Channel 2 Transmit VD     |
| 13                       | TXVG3_2  | Channel 2 Transmit VG3    |
| 14                       | TXVG12_2 | Channel 2 Transmit VG12   |
| 15                       | RXVD_2   | Channel 2 Receive VD      |
| 16                       | RXVG_2   | Channel 2 Receive VG      |
| 18                       | RXOUT_2  | Channel 2 Receive Output  |
| 20                       | TXIN_2   | Channel 2 Transmit Input  |
| 17, 19, 21, 23, 25, Slug | GND      | GROUND                    |

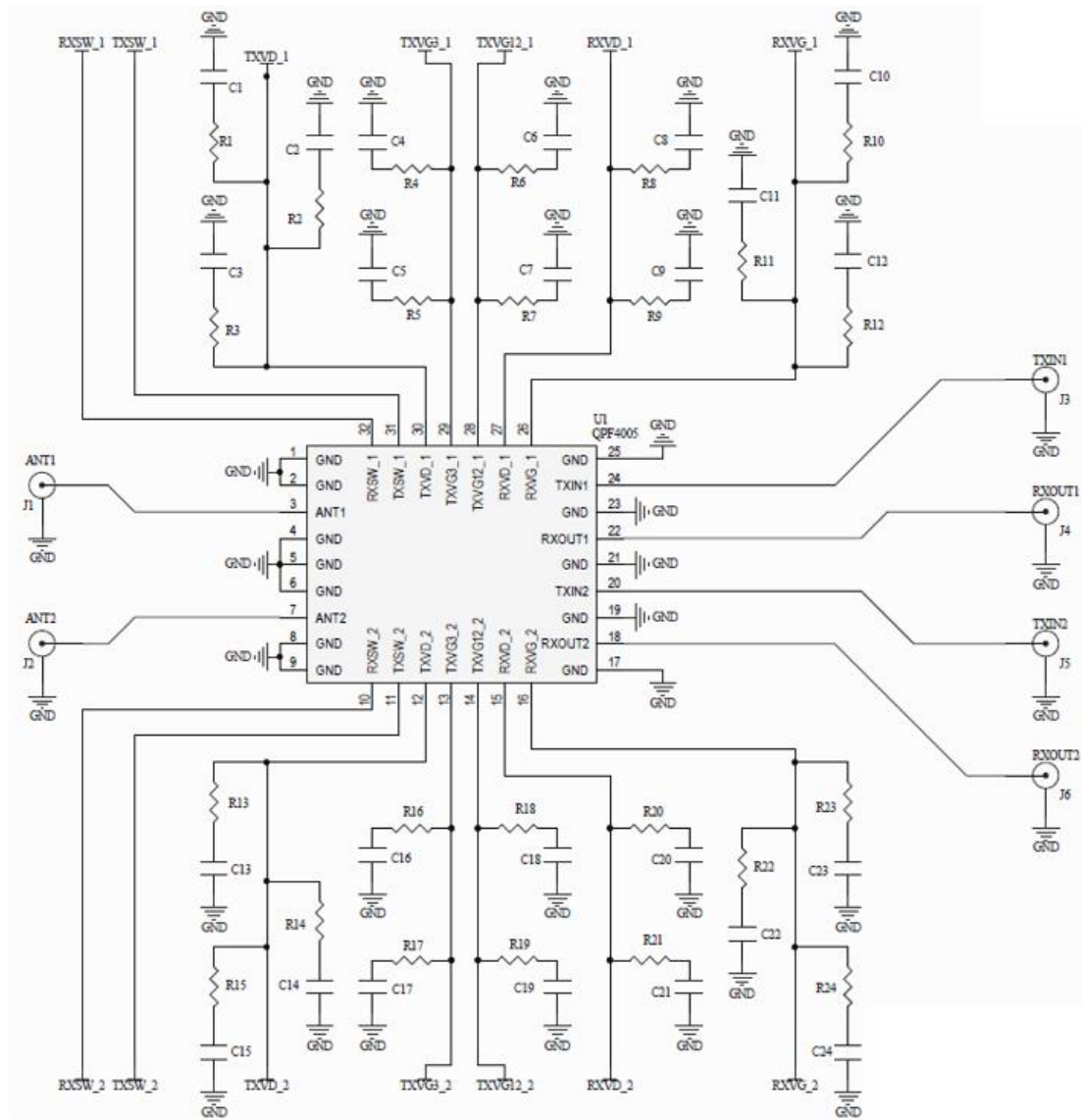
Evaluation Board and Assembly



RF Layer is 0.008" thick Rogers Corp. RO4003C ( $\epsilon_r = 3.35$ ). Metal layers are 0.5 oz. copper. The microstrip line at the connector interface is optimized for the Southwest Microwave end launch connector 1492-04A-5.

| Ref. Des.           | Component | Value                                     | Manuf.  | Remark |
|---------------------|-----------|-------------------------------------------|---------|--------|
| C2, C4, C6, C8, C10 | SMT Cap.  | CAP, 0402 1000pF +/-10% 50V 0402 X7R ROHS | Various | Red    |
| C1, C3, C5, C7, C9  | SMT Cap.  | CAP, 1206 1.0uF +/-10% 50V X7R ROHS       | Various | Grey   |
| R2, R4, R6 - R10    | SMT Res.  | RES, 0402 5.1 OHM, 5% 50V, ROHS           | Various | Green  |
| R1, R3, R5          | SMT Res.  | RES, 0402 0 OHM, 5%, ROHS                 | Various | Pink   |

### Application Circuit



### Bias-up Procedure

1. Set drain supply TXVD limit to 700 mA, RXVD limit to 50 mA, gate and control supply limit to 10 mA each.
2. Set TXVG12, TXVG3, RXVG to -5 V
3. Set TXSW = 20 V (or 0 V), RXSW = 0 V (or 20 V)
4. Set VD = +20 V
5. For TX, adjust TXVG12 to get TXID12 current, then adjust TXVG3 to achieve required total drain current; For RX, adjust RXVG to achieve required drain current.
6. Apply RF signal

### Bias-down Procedure

1. Turn off RF signal
2. Set TXVG12, TXVG3 and RXVG to -5 V
3. Set VD = 0 V
4. Turn off drain supply
5. Turn off TXSW, RXSW
6. Turn off gate supply

### Absolute Maximum Ratings

| Parameter                            | Value         |
|--------------------------------------|---------------|
| Drain Voltage (TXVD, RXVD)           | 28 V          |
| Drain Current (TXID3+TXID12)         | 800 mA        |
| Drain Current (RXID)                 | 60 mA         |
| Gate Voltage (RXVG, TXVG3, TXVG12)   | 0 to -5 V     |
| Gate Current (RXIG, TXIG3, TXIG12)   | 20 mA         |
| Switch Control Voltage (TXSW, RXSW)  | 0 to 28 V     |
| Switch Control Current               | 20 mA         |
| RF Input Power (All RF ports, 85 °C) | 30 dBm        |
| Channel Temperature, T <sub>CH</sub> | 225 °C        |
| Mounting Temperature (30 seconds)    | 260 °C        |
| Storage Temperature                  | -55 to 150 °C |

Operation of this device outside the parameter ranges given above may cause permanent damage. These are stress ratings only, and functional operation of the device at these conditions is not implied. Extended application of Absolute Maximum Rating conditions to the device may reduce device reliability.

### Thermal and Reliability Information

| Parameter                                                                 | Values | Units | Conditions                                                                                                                                                                                          |
|---------------------------------------------------------------------------|--------|-------|-----------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------|
| Thermal Resistance ( $\theta_{JC}$ ) <sup>(1,2,3)</sup> , Quiescent, TX   | 14.9   | °C/W  | TX on, RX off, CW, V <sub>D</sub> = +20 V, I <sub>DQ</sub> = 159 mA, T <sub>BASE</sub> = 85 °C<br>RF off, P <sub>DISS</sub> = 3.18 W                                                                |
| Channel Temperature (T <sub>CH</sub> ), Quiescent, TX                     | 132.4  | °C    |                                                                                                                                                                                                     |
| Thermal Resistance ( $\theta_{JC}$ ) <sup>(1,2,3)</sup> , Under Drive, TX | 10.7   | °C/W  | TX on, RX off, CW, V <sub>D</sub> = +20 V, T <sub>BASE</sub> = 85 °C, Freq = 39 GHz, P <sub>IN</sub> = 10 dBm, P <sub>OUT</sub> = 25 dBm, I <sub>D_DRIVE</sub> = 0.25 A, P <sub>DISS</sub> = 4.69 W |
| Channel Temperature (T <sub>CH</sub> ), Under Drive, TX                   | 135.2  | °C    |                                                                                                                                                                                                     |
| Thermal Resistance ( $\theta_{JC}$ ) <sup>(1,2,3)</sup> , Quiescent, RX   | 67.0   | °C/W  | RX on, TX off, CW, V <sub>D</sub> = +20 V, I <sub>DQ</sub> = 15 mA, T <sub>BASE</sub> = 85 °C<br>RF off, P <sub>DISS</sub> = 0.3 W                                                                  |
| Channel Temperature (T <sub>CH</sub> ), Quiescent, RX                     | 105.1  | °C    |                                                                                                                                                                                                     |

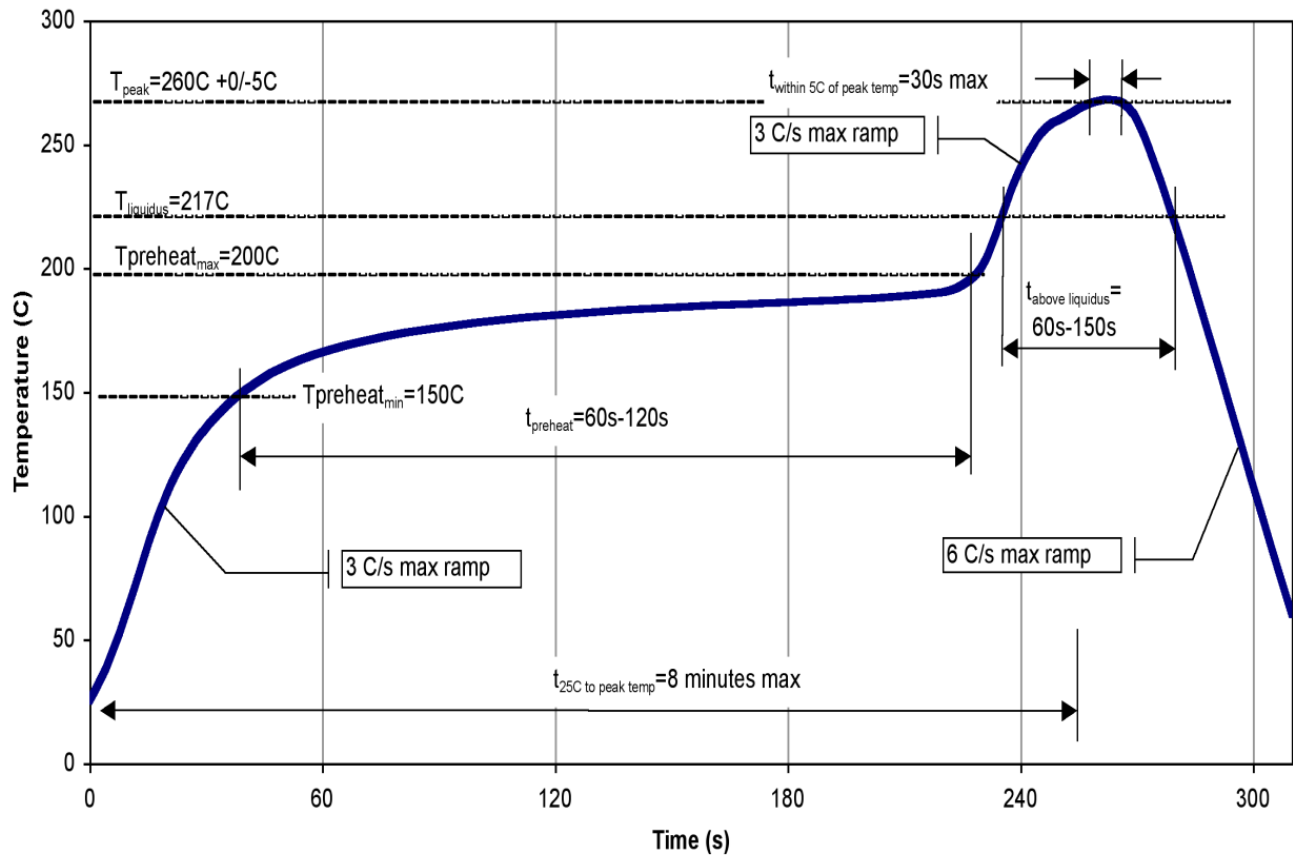
Notes:

1. Thermal resistance is measured to package backside
2. Base or ambient temperature is 85 °C
3. Refer to the following document: [GaN Device Channel Temperature, Thermal Resistance, and Reliability Estimates](#)

## Solderability

1. Compatible with the latest version of J-STD-020, Lead-free solder, 260 °C.
2. The use of no-clean solder to avoid washing after soldering is recommended.

## Recommended Soldering Temperature Profile



### Handling Precautions

| Parameter                        | Rating | Standard                           |
|----------------------------------|--------|------------------------------------|
| ESD – Human Body Model (HBM)     | 0B     | ESDA / JEDEC JS-001-2012           |
| ESD – Charged Device Model (CDM) | C1     | ESDA / JEDEC JS-002-2014           |
| MSL – Convection Reflow 260 °C   | 5A     | JEDEC standard IPC/JEDEC J-STD-020 |



Caution!  
ESD-Sensitive Device

### RoHS Compliance

This product is compliant with the 2011/65/EU RoHS directive (Restrictions on the Use of Certain Hazardous Substances in Electrical and Electronic Equipment), as amended by Directive 2015/863/EU. This product also has the following attributes:

- Lead Free
- TBBP-A (C<sub>15</sub>H<sub>12</sub>Br<sub>4</sub>O<sub>2</sub>) Free
- PFOS Free

### Contact Information

For the latest specifications, additional product information, worldwide sales and distribution locations:

**Tel:** 1-844-890-8163

**Web:** [www.qorvo.com](http://www.qorvo.com)

**Email:** [customer.support@qorvo.com](mailto:customer.support@qorvo.com)

For technical questions and application information: **Email:** [appsupport@qorvo.com](mailto:appsupport@qorvo.com)

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